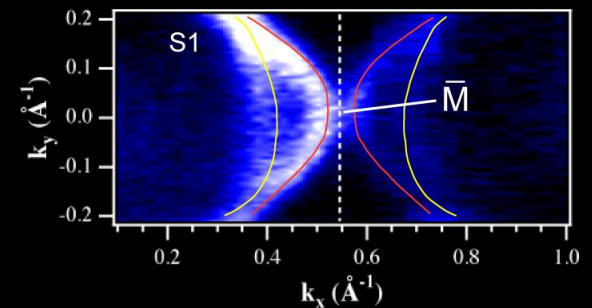
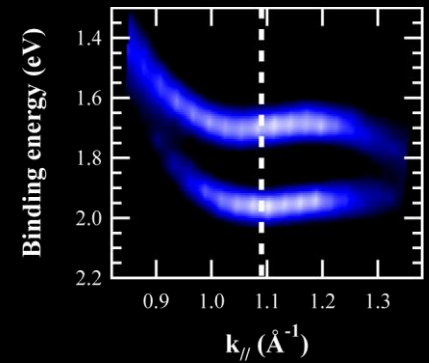
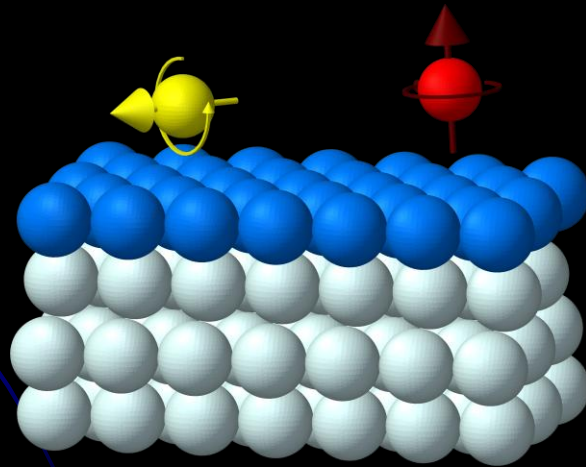


対称性に起因する特異なRashba効果

坂本一之

千葉大学大学院融合科学研究科



対称性に起因する特異なRashba効果

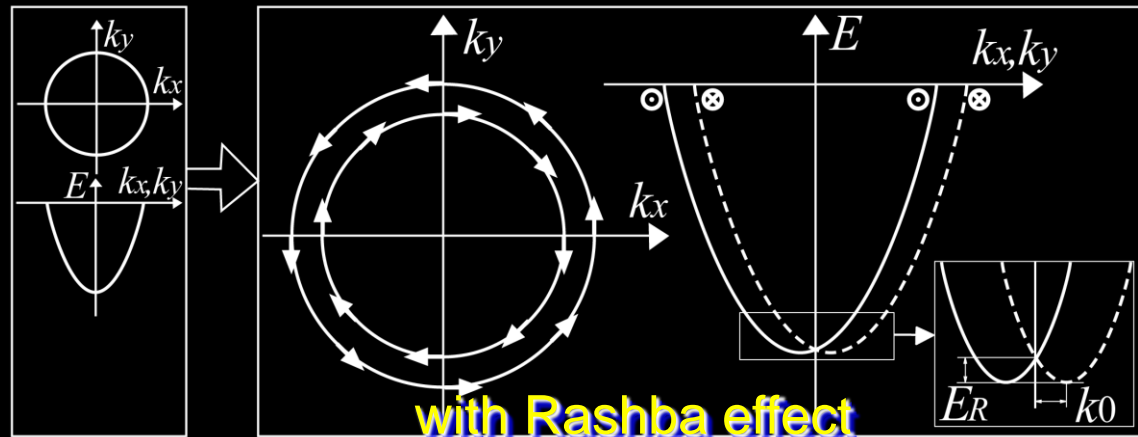
坂本一之

千葉大学大学院融合科学研究科

Outline

1. Introduction
2. Results and discussion
TI/Si(111)-($\sqrt{3}\times\sqrt{3}$), -(1x1)
(PRL 102, 096805 (2009), PRB 74, 075335 (2006))
Bi/Si(111)-($\sqrt{3}\times\sqrt{3}$)
(PRL 103, 156801 (2009))
3. Conclusion

Introduction; Rashba effect



$$[E(k, \uparrow) = E(-k, \downarrow)]$$

time-reversal symmetry

$$H_{RB} = \alpha_R (|\varepsilon|) \sigma \cdot (\mathbf{k}_{\parallel} \times \hat{e}_z)$$

α_R ; Rashba parameter

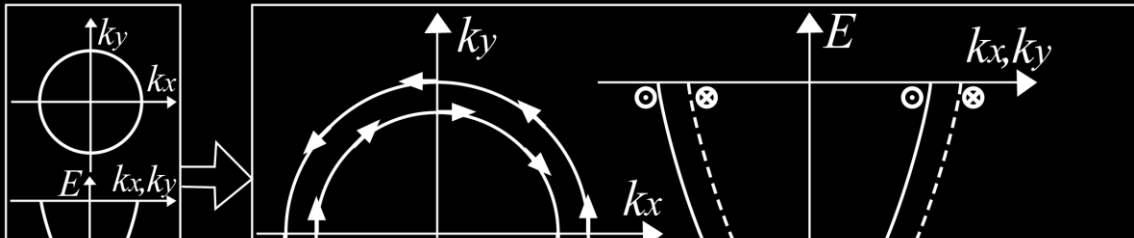
$$\alpha_R = \hbar^2 k_0 / m^*$$

σ ; Pauli spin matrices

ε ; electric field determined by the potential gradient

Y.A. Bychkov and E.I. Rashba,
JETP Lett. 39, 78 (1984).

Introduction; Rashba effect



元素周期表
Periodic Table of the Elements
自然も暮らしもすべて元素記号で書かれている

Materials

Ag(111)

, 045419 (2005)

Au(111)

, 195413 (2006)

Bi(111)

PRB 73, 195413 (2006)

Tl on a Si(111) surface
Bi on a Si(111) surface

PRB 57, 3419 (1996)

, 046403 (2004)

Bi/Ag(111)

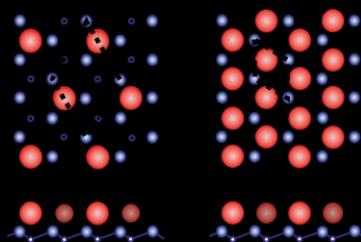
PRL 98, 186807 (2007)

Introduction; Tl/Si(111)

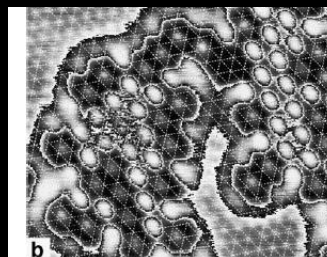
Group III metals (Al, Ga, and In) on Si(111);
 magic cluster arrays at modest temperature (PRL 81, 164 (1998))
 $(\sqrt{3} \times \sqrt{3})$ reconstruction at higher temperature (PRL 81, 164 (1998))

Tl; peculiar behavior in the form of the so-called “inert pair effect”
 On a Si(111) surface; 1ML (1x1) phase monovalent atom
 1/3 ML $(\sqrt{3} \times \sqrt{3})$ phase **trivalent**

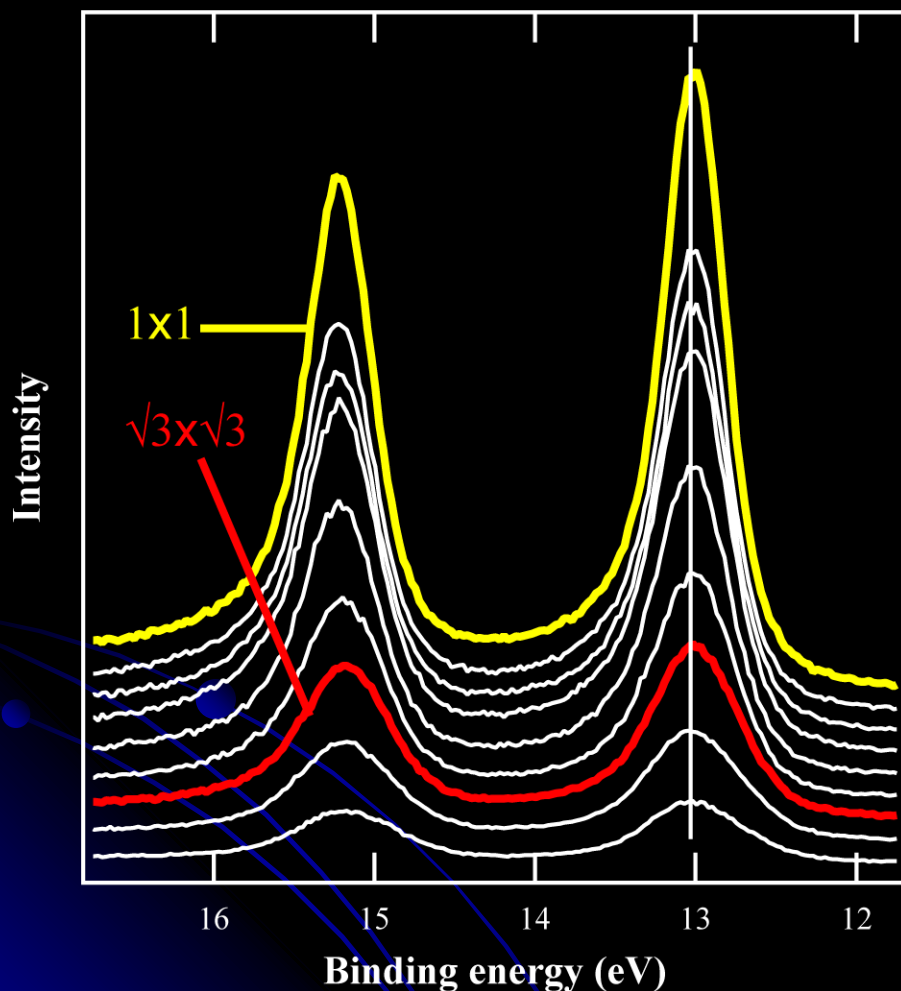
variable valency for Tl on a Si(111) ?
 (SS 543, L663 (2003), PRB 66, 233312 (2002))



SS 543, L663 (2003)



Results; Tl 5d core-level



$$I_{(1 \times 1)} : I_{(\sqrt{3} \times \sqrt{3})} = 3 : 1$$

(1x1) surface; **1ML**,
 ($\sqrt{3} \times \sqrt{3}$) surface; **1/3 ML**

constant binding energy

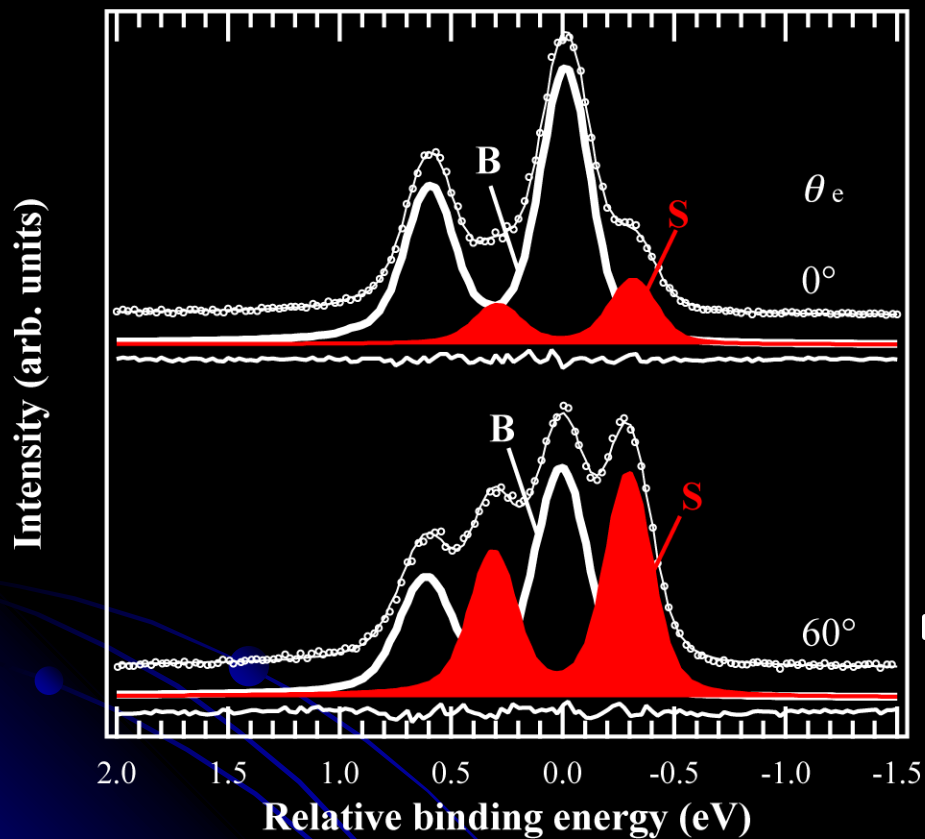
difference in E_B of the
 5d core-level for the Tl^{1+}
 and Tl^{3+} is 0.58 eV
 J.Phys.Soc.Jpn., 73, 1532 (2004)



Identical valence state

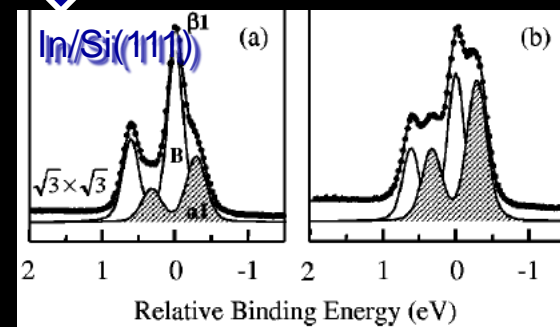
Coverage-dependent Tl 5d core-level spectra
 obtained with a photon energy of 50 eV.

Results; $Tl/Si(111)-(1 \times 1)$ Si 2p core-level



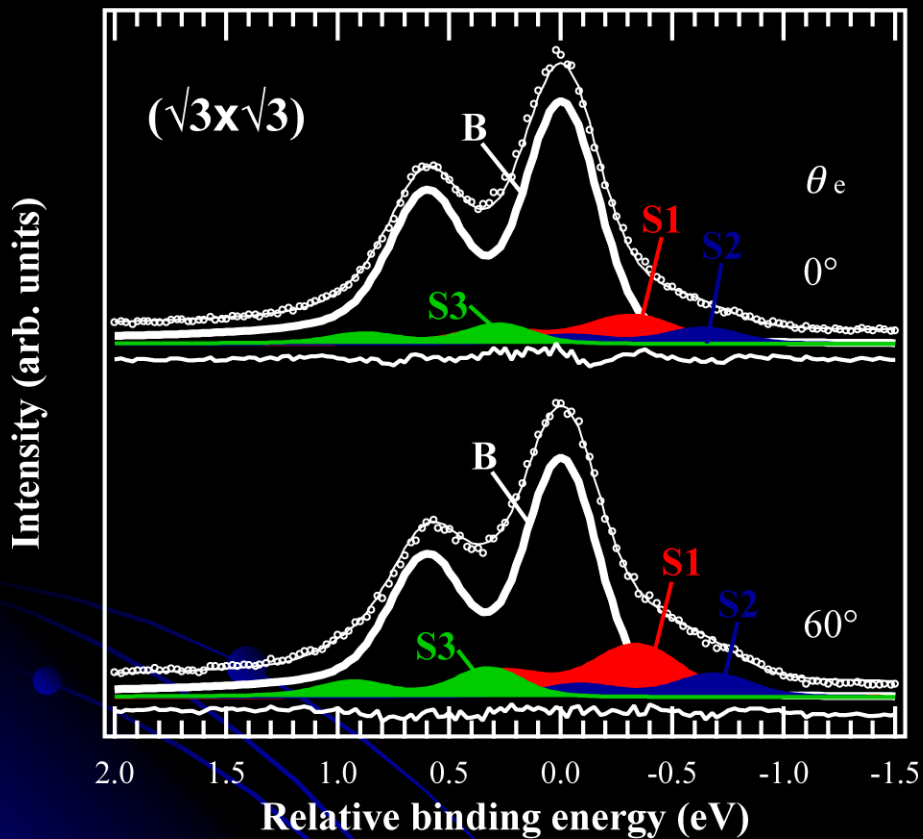
Si 2p core-level spectra of the $Tl/Si(111)-(1 \times 1)$ surface measured with $h\nu=135$ eV.

common unreconstructed (1×1) structure



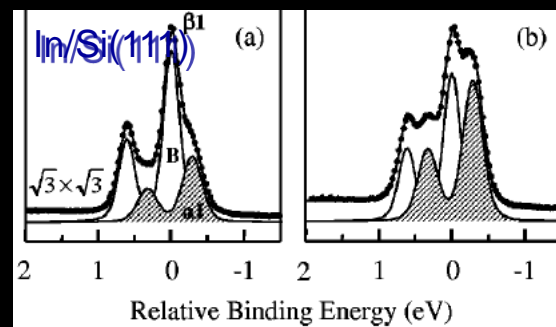
PRB 67, 035414 (2003)

Results; $Tl/Si(111)-(\sqrt{3}\times\sqrt{3})$ Si 2p core-level



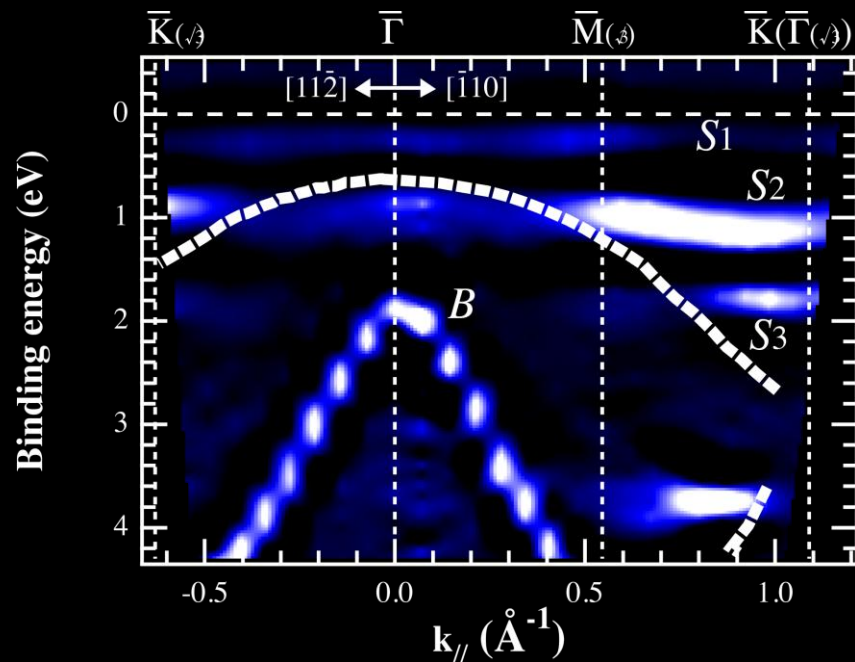
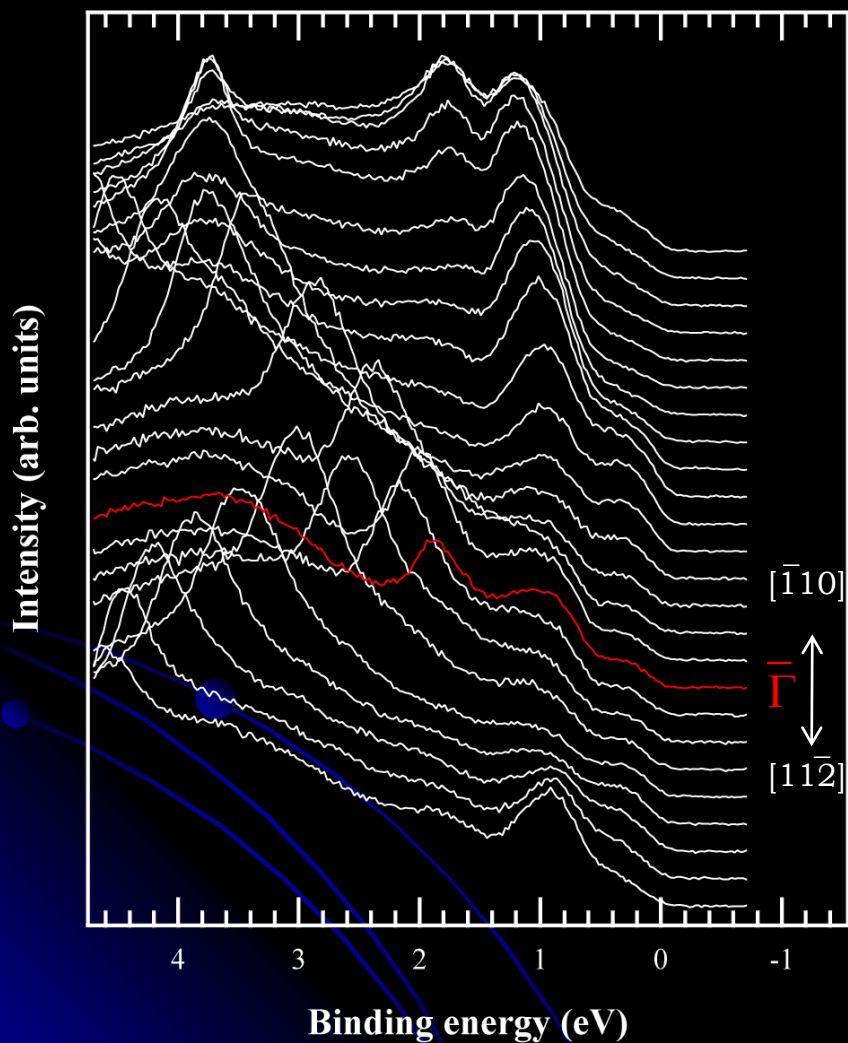
Si 2p core-level spectra of the $Tl/Si(111)-(\sqrt{3}\times\sqrt{3})$ surface measured with $h\nu=135$ eV.

the two $(\sqrt{3}\times\sqrt{3})$ surfaces have **different atomic structures**



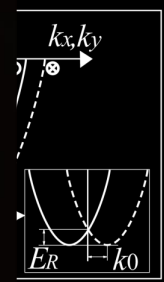
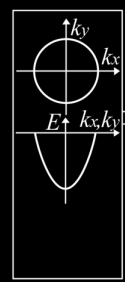
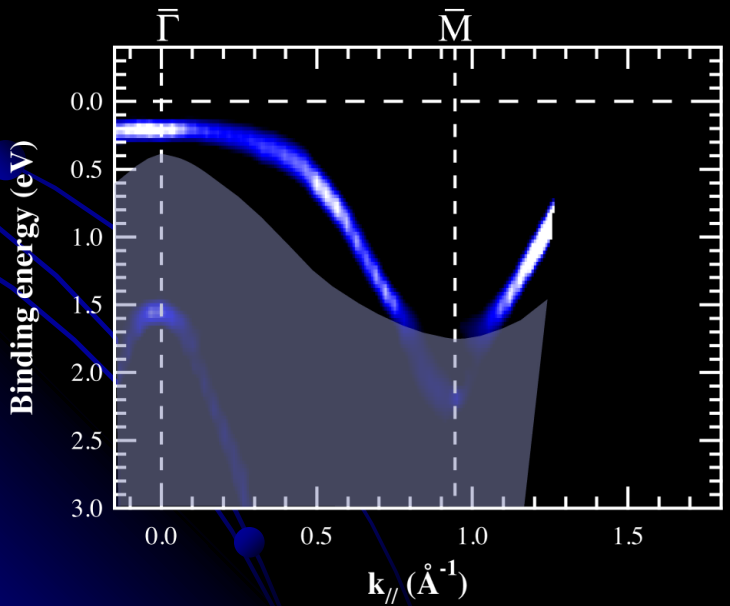
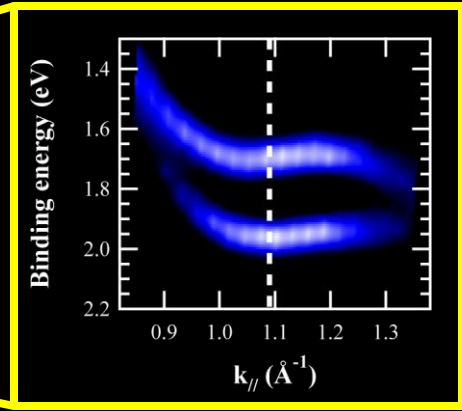
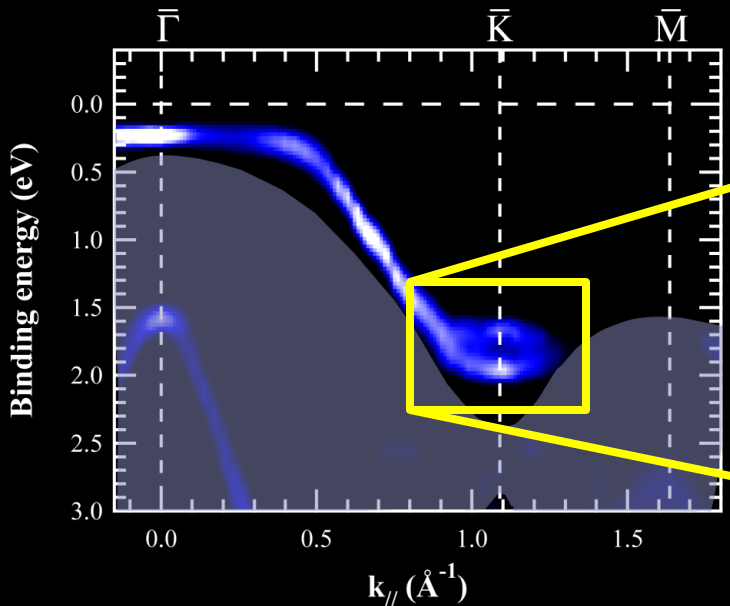
PRB 67, 035414 (2003)

Results: $Tl/Si(111)-(\sqrt{3}\times\sqrt{3})$ ARPES



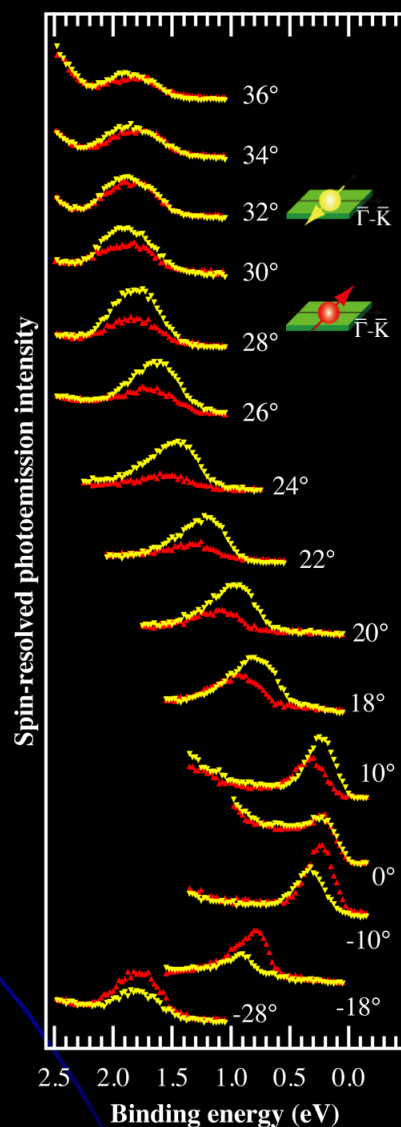
ARPES spectra measured using $h\nu=21.2$ eV

Results; $Tl/Si(111)-(1 \times 1)$ valence band



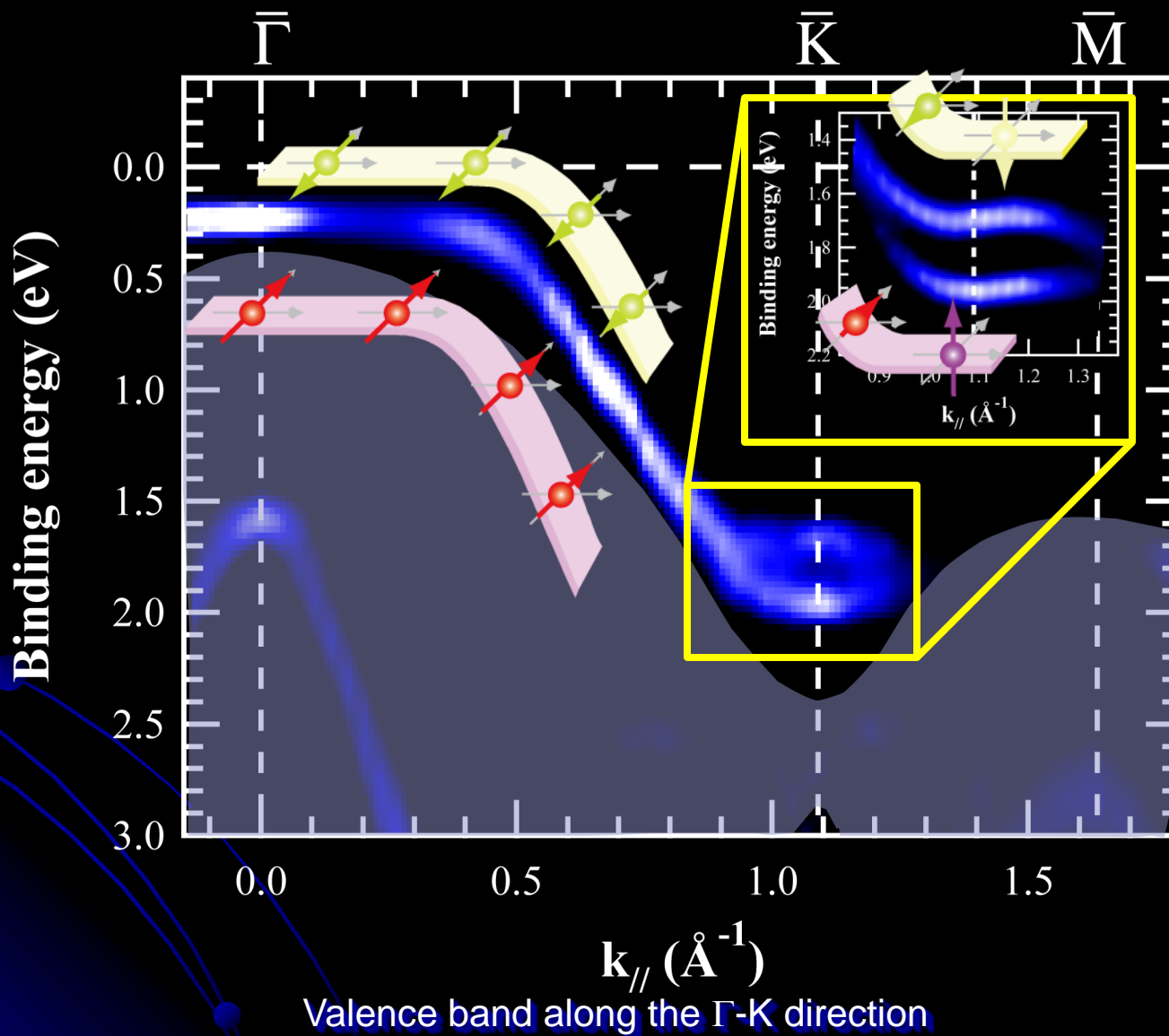
Band dispersions along the Γ -K and Γ -M directions

Results; $Tl/Si(111)-(1 \times 1)$ SR-ARPES



SR-ARPES spectra measured along the Γ -K direction

Results; $Tl/Si(111)-(1 \times 1)$ spin states



Discussion, extended RB effect

$$\varphi_{n\mathbf{k}}(\mathbf{r}) = \frac{1}{\sqrt{\Omega}} \exp(i\mathbf{k} \cdot \mathbf{r}) u_{n\mathbf{k}}(\mathbf{r})$$

Effective SOI Hamiltonian of the “extended RB effect”

$$H_{SOI}(\mathbf{k}) = \boldsymbol{\sigma} \cdot (\boldsymbol{\alpha}_n(\mathbf{k}) \times \mathbf{k}) + \boldsymbol{\sigma} \cdot \underline{\mathbf{B}}_n(\mathbf{k})$$

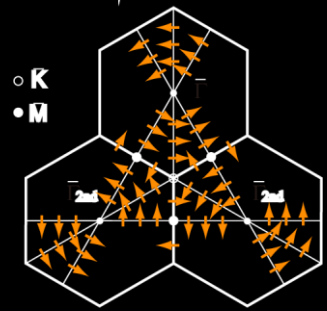
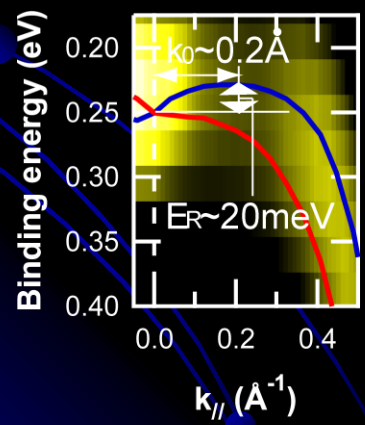
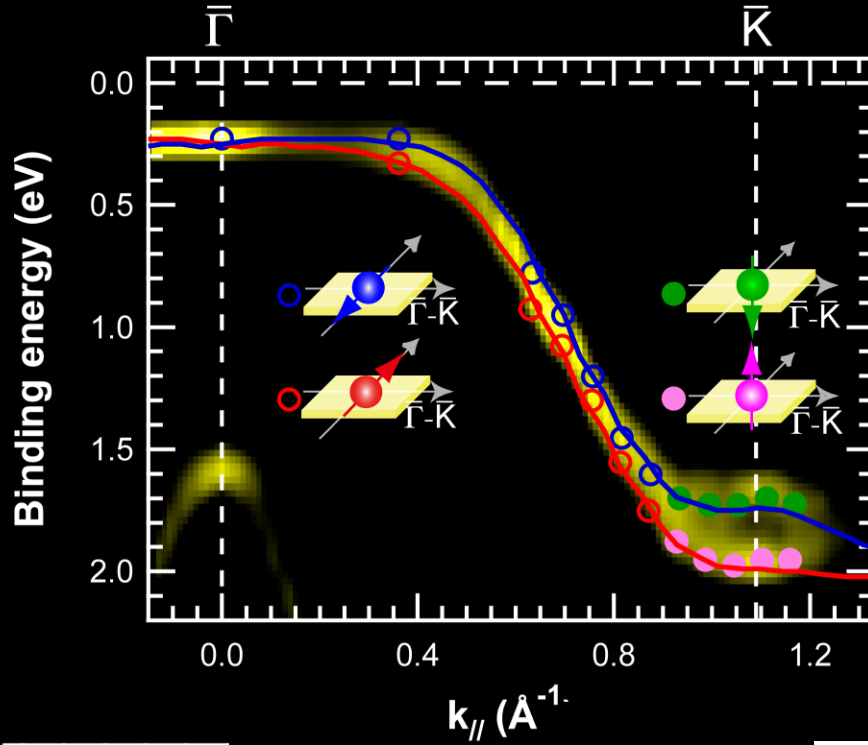


$$H_{RB} = \alpha_R (|\varepsilon|) \boldsymbol{\sigma} \cdot (\mathbf{k}_{||} \times \hat{e}_z)$$

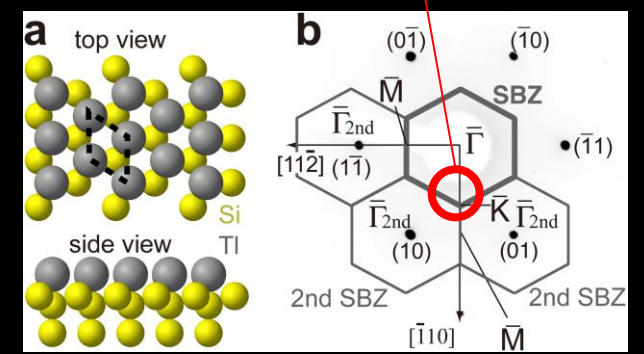
$$\vec{\alpha}_n(\vec{k}) = \frac{\hbar^2 N}{4m_e^2 c^2 \Omega} \int_{cell} d\vec{r} |u_{n\vec{k}}(\vec{r})|^2 \nabla V(\vec{r})$$

$$\vec{B}_n(\vec{k}) = \frac{\hbar^2 N}{4m_e^2 c^2 \Omega} \int_{cell} d\vec{r} \frac{1}{r} \frac{dV(\vec{r})}{dr} u_{n\vec{k}}^*(\vec{r})(\vec{l}) u_{n\vec{k}}(\vec{r})$$

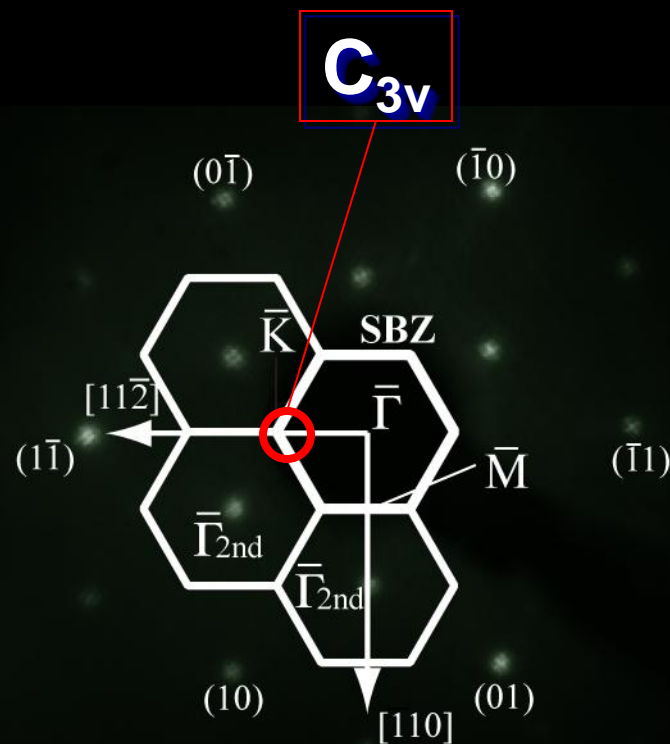
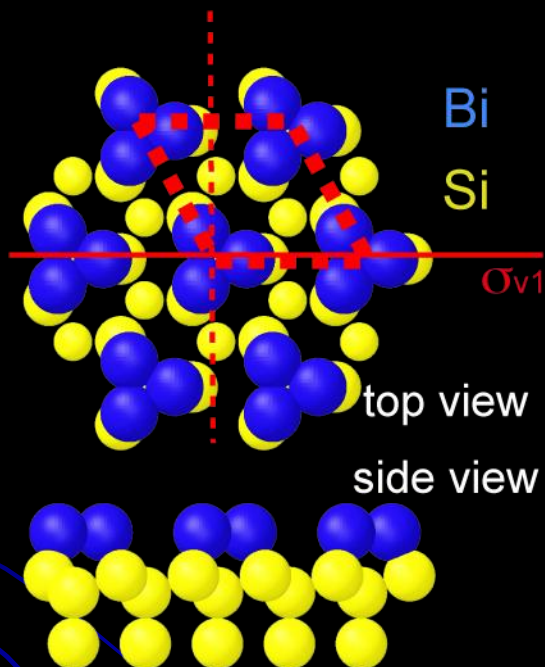
Discussion, origin of the standing spin



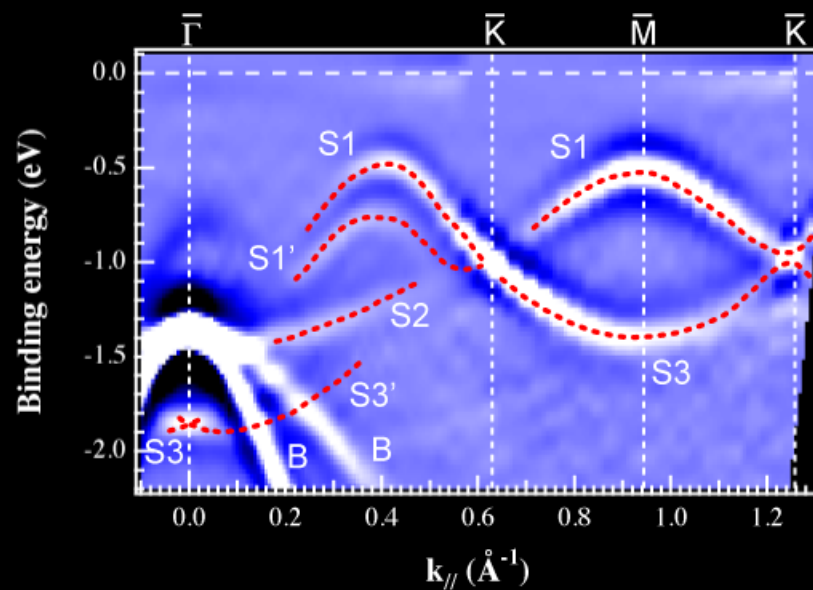
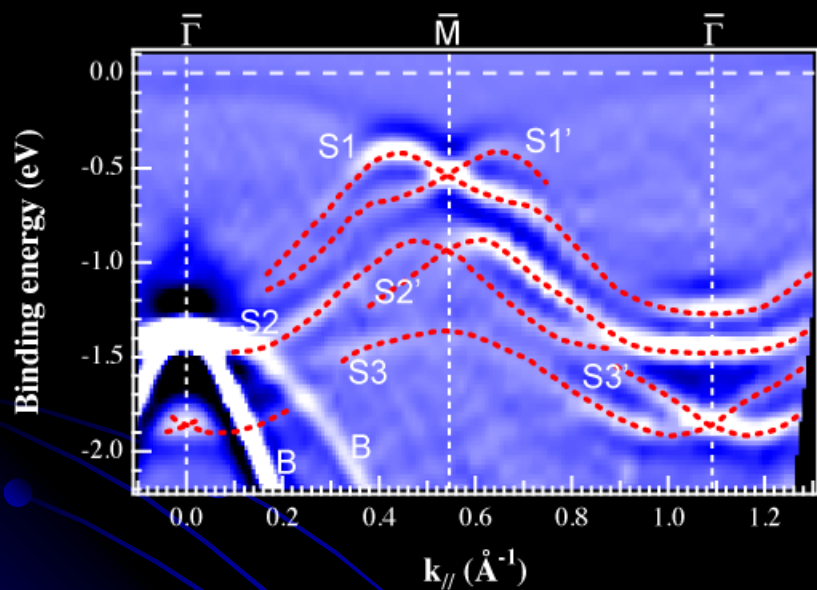
C_3



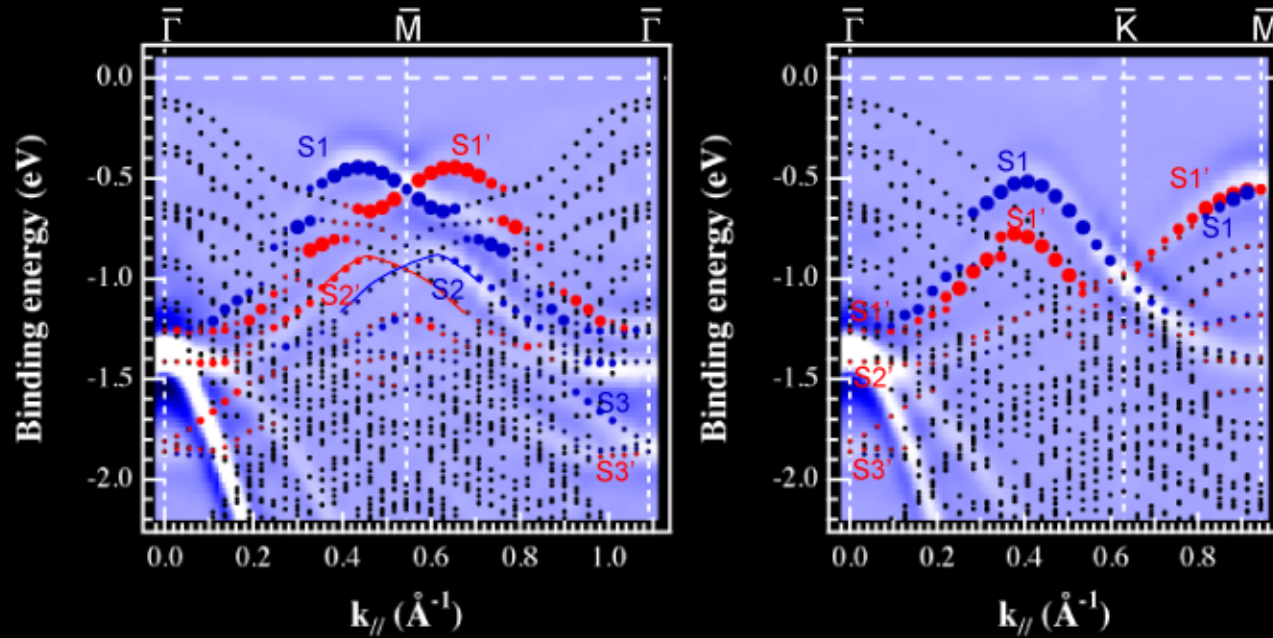
Introduction; Bi/Si(111)-($\sqrt{3}\times\sqrt{3}$)



Results; Bi/Si(111)-($\sqrt{3}\times\sqrt{3}$) ARPES

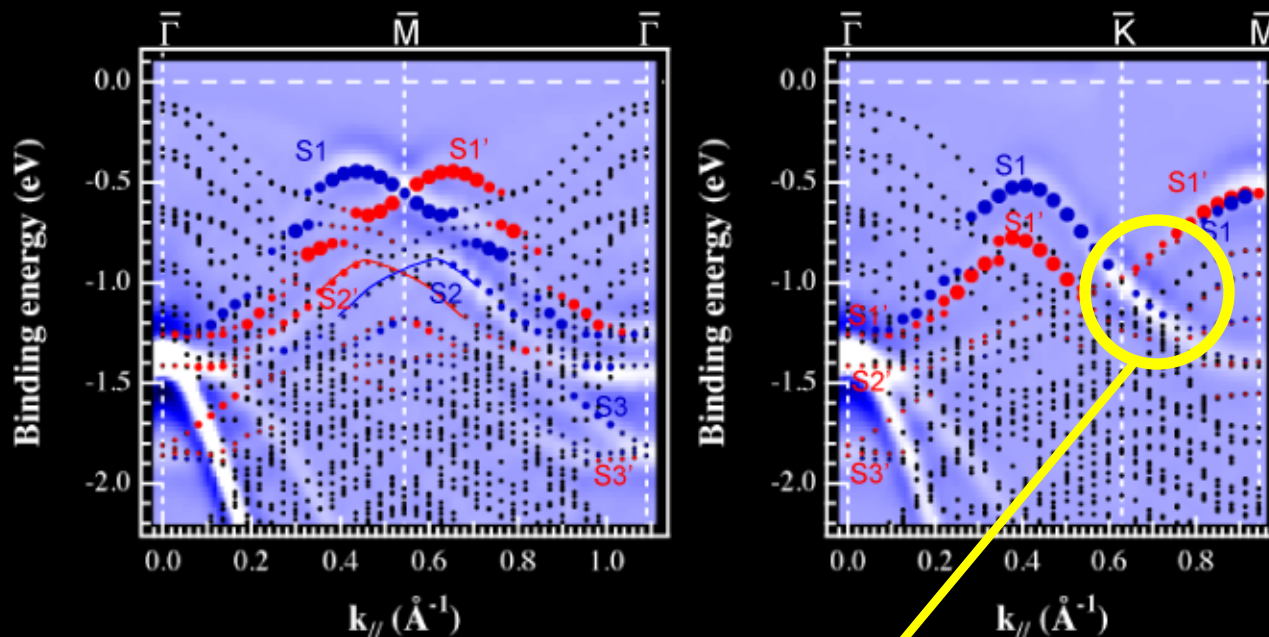


Results; Bi/Si(111)-($\sqrt{3}\times\sqrt{3}$) ARPES



Materials	E_R (meV)	k_0 (\AA^{-1})	
S1	120	0.105	I. Gierz <i>et al.</i> , PRL 103, 046803 (2009)
S2	70	0.08	
S3	70	0.08	
Bi/Ag(111)	200	0.13	C. Ast <i>et al.</i> , PRL 98, 186807 (2007)

Results; Bi/Si(111)-($\sqrt{3}\times\sqrt{3}$) ARPES



Observation of a Rashba splitting though there is no time reversal

Materials

E_P (meV)

k_0 (\AA^{-1})

I. Gierz *et al.*, PRL 103, 046803 (2009)

S1

120

0.105

Peculiar Rashba splitting

that originates from the

C_{3v} symmetry

S2

70

0.08

S3

70

0.08

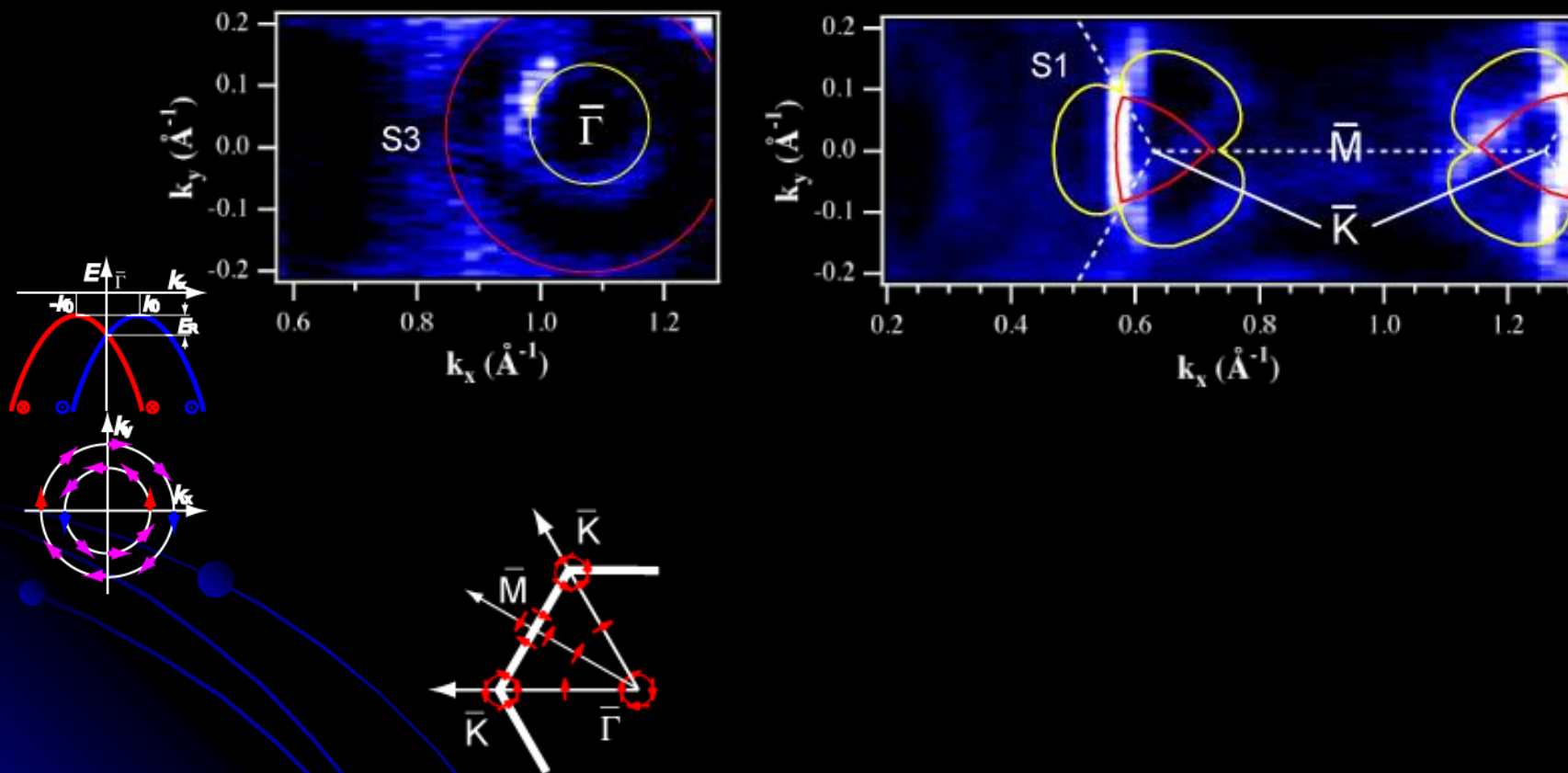
Bi/Ag(111)

200

0.13

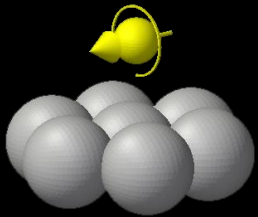
C. Ast *et al.*, PRL 98, 186807 (2007)

Results; Bi/Si(111)-($\sqrt{3}\times\sqrt{3}$) ARPES

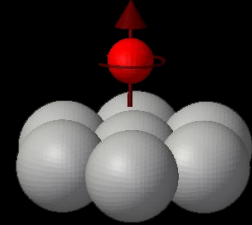


Conclusion

Observation of **peculiar Rashba spins**



Tl/Si(111)-(1x1)
Spin **standing perpendicular**



Bi/Si(111)-($\sqrt{3} \times \sqrt{3}$)
Rashba spin at a point **without time-reversal symmetry**
Non-vortical Rashba spin structure



knowledge on the 2D symmetry is indispensable
to understand the Rashba effect properly

Acknowledgments

Experiment team

Chiba University, Japan,

A. Imai, H. Kakuta, T. Kuzumaki, N. Ueno

Hiroshima University, Japan

A. Kimura, K. Miyamoto, H. Namatame, M. Taniguchi

Tohoku University, Japan

K. Sugawara, T. Sato, T. Takahashi

Linkoping University, Sweden

P.E.J. Eriksson, R.I.G. Uhrberg

TASC National Lab., Italy

E. Annese, J. Fujii

¥¥ Financial supports ¥¥
JSPS Grant-in-Aid for
Scientific Research (A)
20244045 and (B)
20340092, and the G-COE
program of MEXT (G-03)

Theory team

Kanazawa University, Japan

T. Oda, M. Tsujikawa

Hiroshima University, Japan

A. Kodama, T. Shishidou, T. Oguchi